

### FTS1001-VB Datasheet

## Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)			
- 30	0.036 at V <sub>GS</sub> = - 10 V	- 5.2			
	0.055 at V <sub>GS</sub> = - 4.5 V	- 4.2			

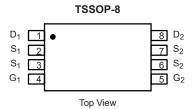
#### FEATURES

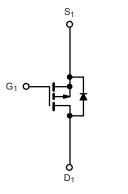
- Halogen-free
- Trench Power MOSFETs

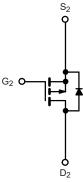
#### APPLICATIONS

Load SwitchBattery Switch









P-Channel MOSFET

P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b>	T <sub>A</sub> = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 30		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
	T <sub>A</sub> = 25 °C	– I <sub>D</sub>	- 5.2	- 4.1	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		- 4.2	- 3.6	
Pulsed Drain Current (10 µs Pulse Width)		I <sub>DM</sub>	- 30		A
Continuous Source Current (Diode Conduction) <sup>a</sup>	IS .		- 1.0	- 1.0 - 0.70	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	PD	1.14	0.83	W
	T <sub>A</sub> = 70 °C	- FD	0.73	0.53	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manimum humatism to Analysism to	t ≤ 10 s	- R <sub>thJA</sub>	86	110	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		124	150	
Maximum Junction-to-Foot	Steady State	R <sub>thJF</sub>	52	65	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1.0		- 3.0	V			
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1				
		$V_{DS}$ = - 30 V, $V_{GS}$ = 0 V, $T_{J}$ = 55 °C			- 10	μA			
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge -5 V$ , $V_{GS} = -10 V$	- 15			А			
	D	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 4.7 A	4.7 A			0			
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 3.8 A		0.055		Ω			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 4.7 A		14		S			
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = - 1.0 A, V <sub>GS</sub> = 0 V		- 0.74	- 1.1	V			
Dynamic <sup>b</sup>									
Total Gate Charge	Qg			13	20				
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = - 15 V, $V_{GS}$ = - 4.5 V, $I_{D}$ = - 4.7 A		3		nC			
Gate-Drain Charge	Q <sub>gd</sub>			5.8		1			
Gate Resistance	Rg	f = 1.0 MHz		4.6		Ω			
Turn-On Delay Time	t <sub>d(on)</sub>			13	20				
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 15 $\Omega$		14	22				
Turn-Off Delay Time	t <sub>d(off)</sub>	${\rm I}_{\rm D}{\cong}$ - 1 A, ${\rm V}_{\rm GEN}$ = - 10 V, ${\rm R}_{\rm G}$ = 6 $\Omega$		52	80	ns			
Fall Time	t <sub>f</sub>			26	40				
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 1.0 A, dl/dt = 100 A/μs		40	60				

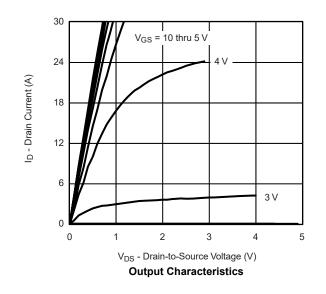
Notes:

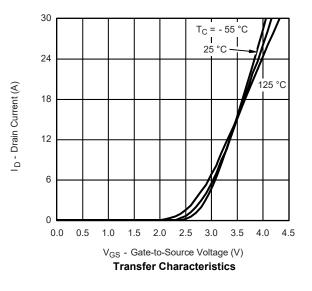
a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

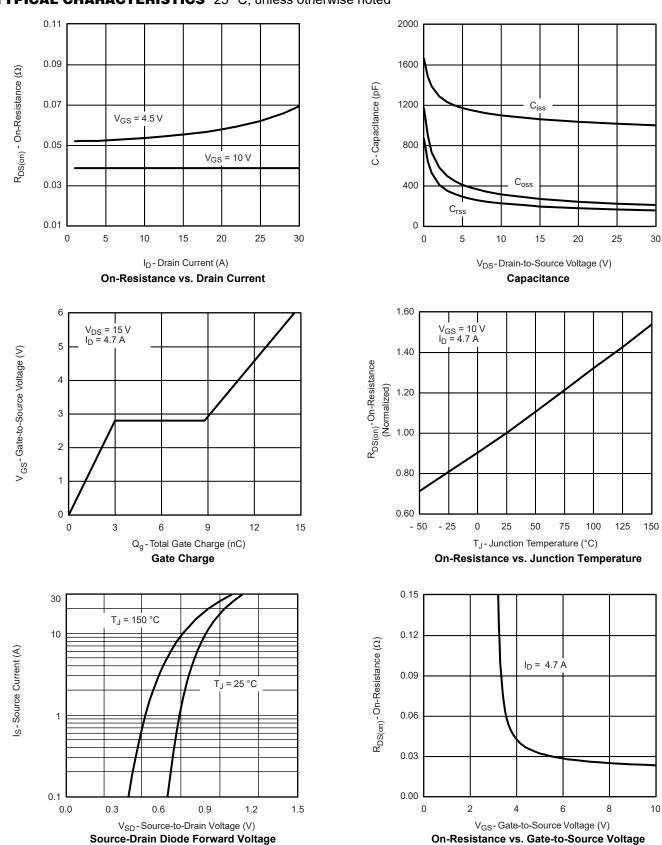
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





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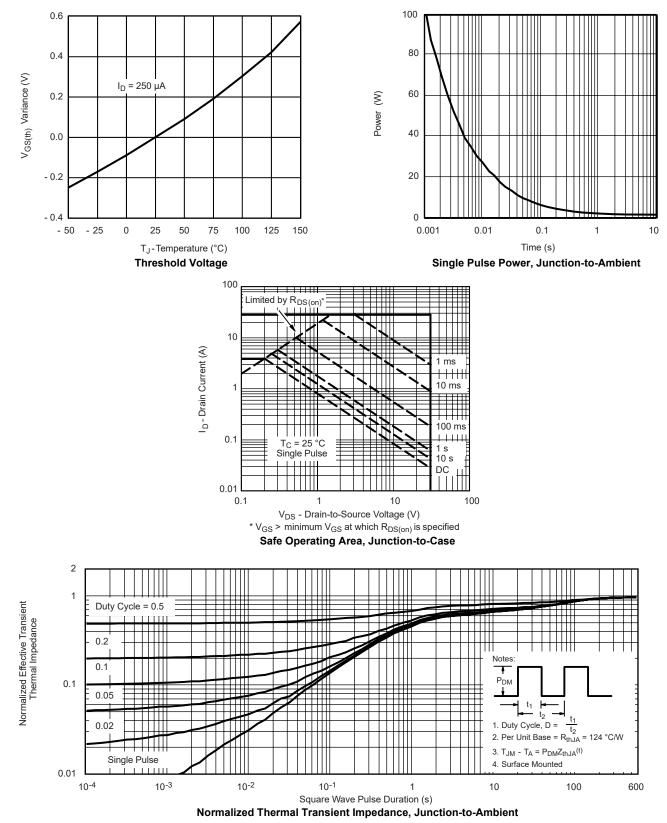




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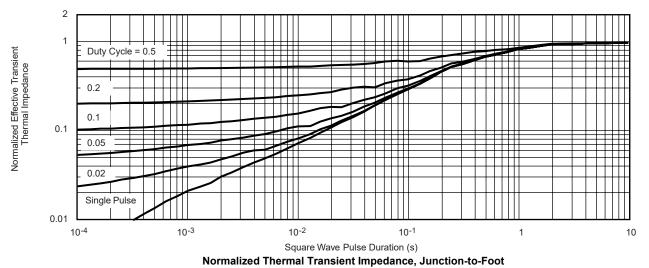


#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



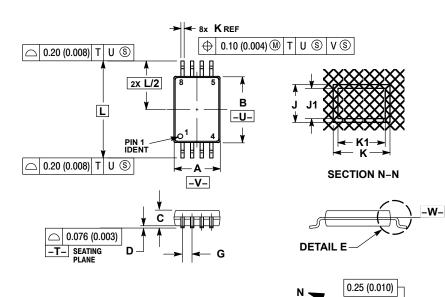


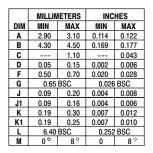
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